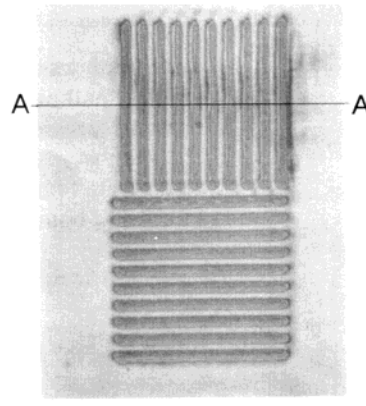
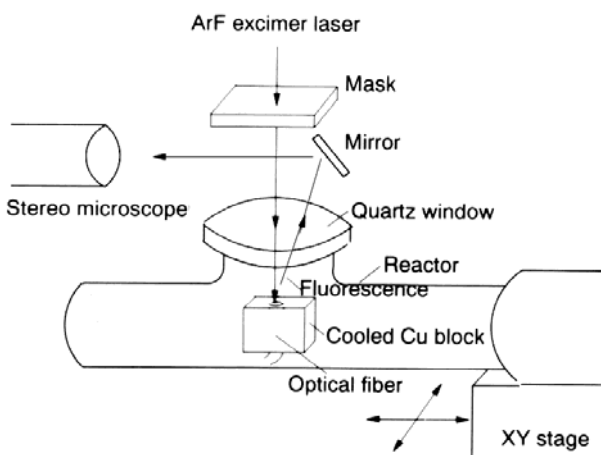
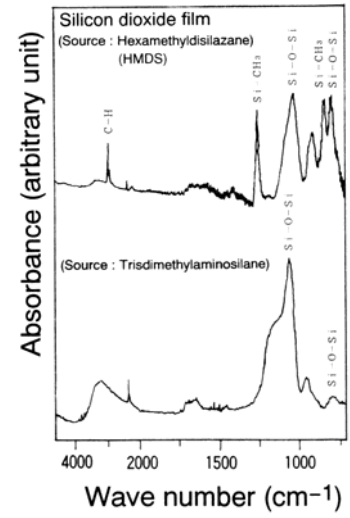


Laser Processes and Stealth Dicing

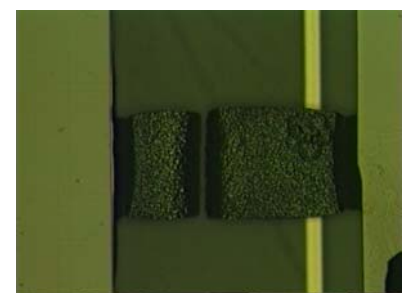
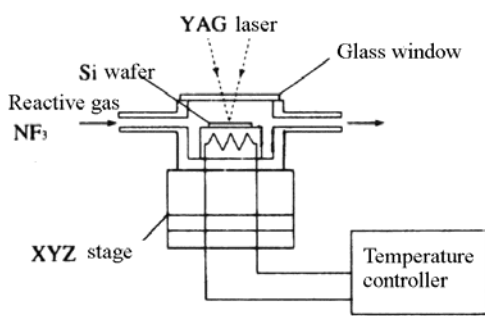
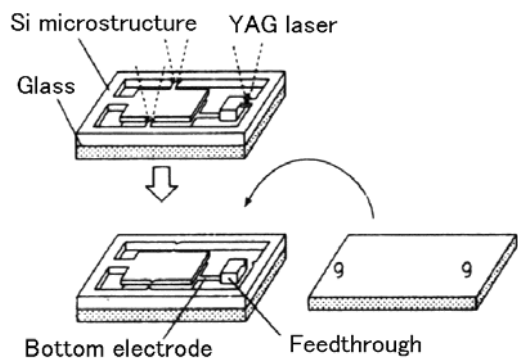


Pressure of HMDS : 470Pa
 Pressure of O₂ : 67Pa
 Substrate temp. : 2 °C
 Laser irradiation time : 2min



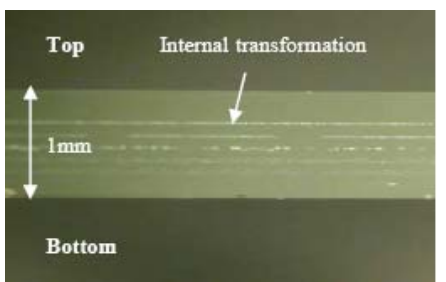
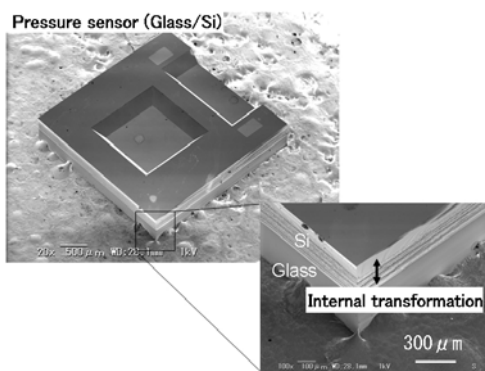
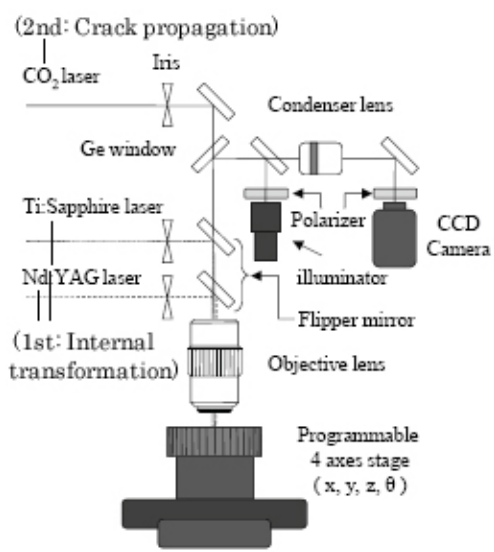
Laser projection CVD

Reference : K.Takashima, K.Minami, M.Esashi and J.Nishizawa, Laser Projection CVD Using the Low Temperature Condensation Method, Applied Surface Science, 79/80 (1994) pp.366-374



Laser assisted Si etching

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Laser (stealth) dicing of Si-glass structure (Tohoku Univ. - Inst. For Laser Tech.)

Reference : M.Fujita, Y.Izawa, Y.Tsurumi, S.Tanaka, H.Fukushi, K.Sueda, Y.Nakata, M.Esashi and N.Miyanaga, Debris-free Low-stress High-speed Laser Assisted Dicing for Multi-layered MEMS, Trans. IEE of Japan, 130-E (2010) pp.118-123